



7N65-CB

Power MOSFET

7.0A, 650V N-CHANNEL POWER MOSFET

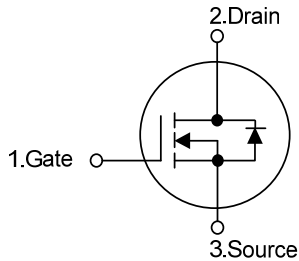
DESCRIPTION

The UTC **7N65-CB** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)} < 1.1 \Omega @ V_{GS} = 10 V, I_D = 3.5 A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL

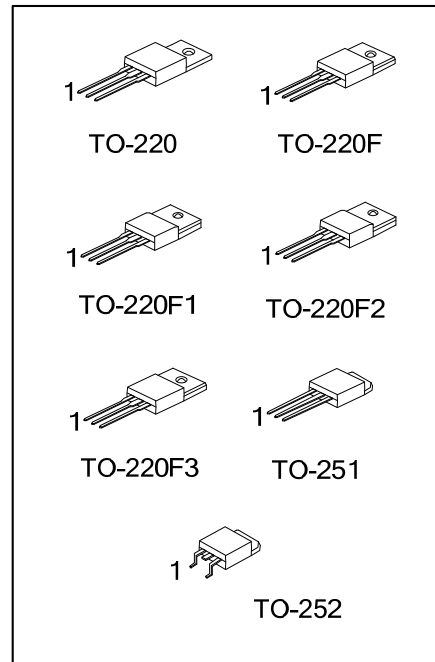


ORDERING INFORMATION

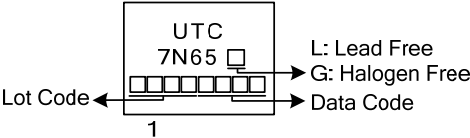
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7N65L-TA3-T	7N65G-TA3-T	TO-220	G	D	S	Tube
7N65L-TF3-T	7N65G-TF3-T	TO-220F	G	D	S	Tube
7N65L-TF1-T	7N65G-TF1-T	TO-220F1	G	D	S	Tube
7N65L-TF2-T	7N65G-TF2-T	TO-220F2	G	D	S	Tube
7N65L-TF3T-T	7N65G-TF3T-T	TO-220F3	G	D	S	Tube
7N65L-TM3-T	7N65G-TM3-T	TO-251	G	D	S	Tube
7N65L-TN3-R	7N65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220F, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, TM3: TO-251, TN3: TO-252</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
--	---



■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	7	A
Continuous Drain Current		I_D	7	A
Pulsed Drain Current (Note 2)		I_{DM}	24	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	245	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.0	V/ns
Power Dissipation	TO-220	P_D	125	W
	TO-220F/TO-220F1		40	W
	TO-220F3			
	TO-220F2		42	W
	TO-251/TO-252		55	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L = 10\text{mH}$, $I_{AS} = 7\text{A}$, $V_{DD} = 90\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 7\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

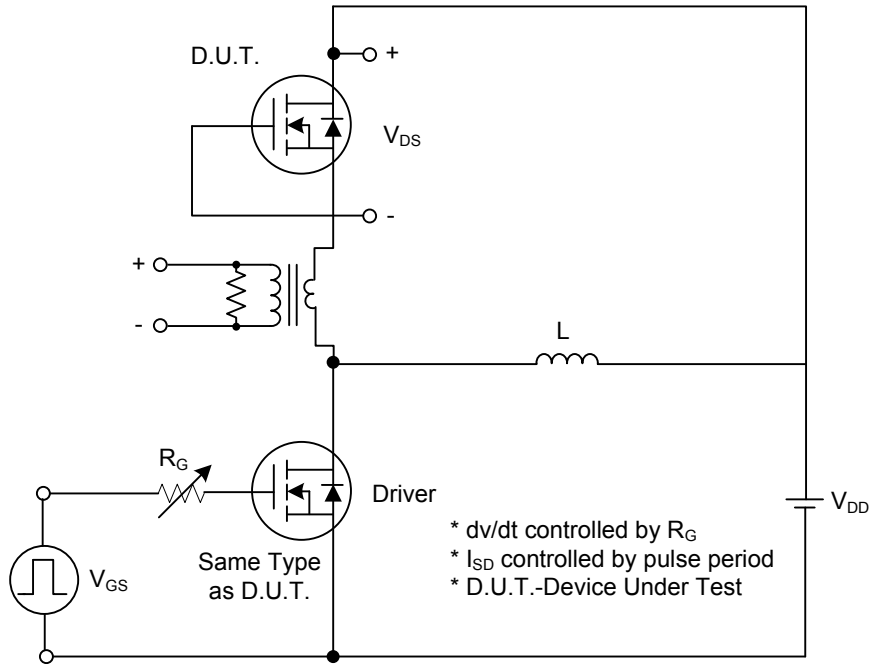
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2			
	TO-220F3			
	TO-251/TO-252		110	
Junction to Case	TO-220	θ_{JC}	1.0	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		3.2	
	TO-220F3			
	TO-220F2		2.97	
	TO-251/TO-252		2.27	

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

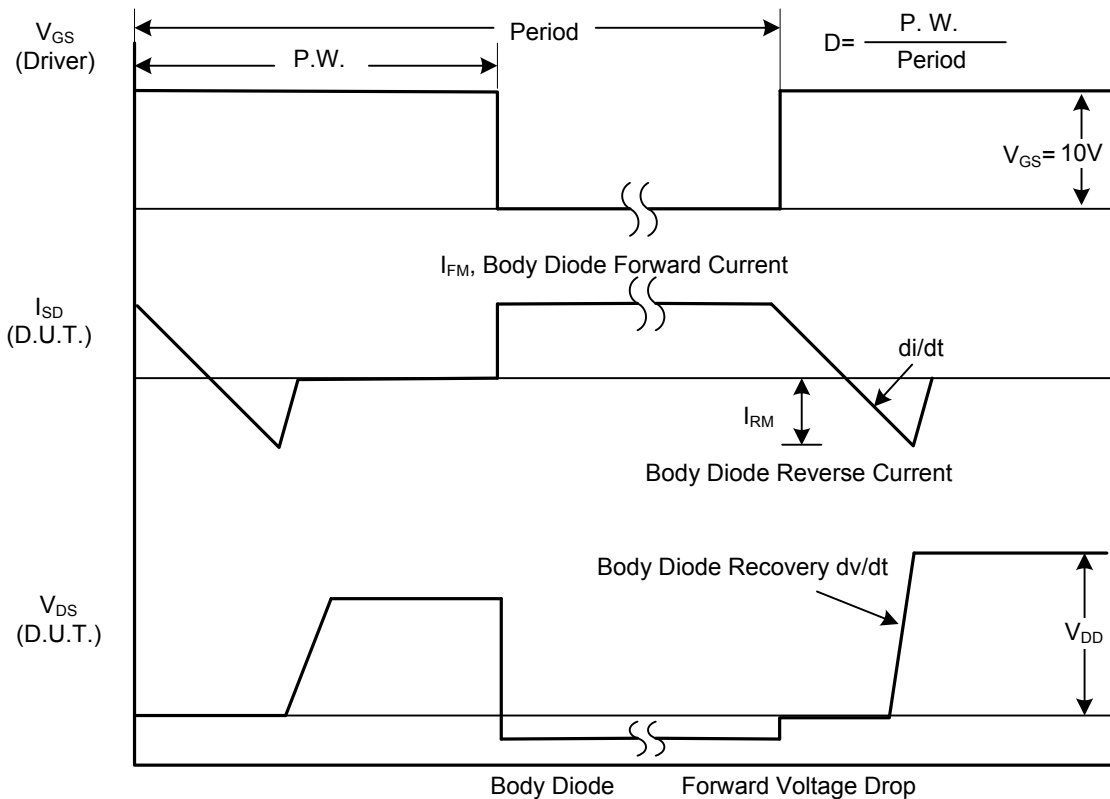
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	650			V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 650V, V _{GS} = 0V			10	μA	
Gate- Source Leakage Current	Forward	I _{GSS}			100	nA	
	Reverse						V _{GS} = 30V, V _{DS} = 0V
		V _{GS} = -30V, V _{DS} = 0V			-100	nA	
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.53		V/°C	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V	
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 3.5A			1.1	Ω	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		359		pF	
Output Capacitance	C _{OSS}				114		pF
Reverse Transfer Capacitance	C _{RSS}				7		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge	Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A, I _D =100μA (Note 1, 2)		118		nC	
Gate-Source Charge	Q _{GS}				8.0		nC
Gate-Drain Charge	Q _{GD}				8.4		nC
Turn-On Delay Time	t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		48		ns	
Turn-On Rise Time	t _R				36		ns
Turn-Off Delay Time	t _{D(OFF)}				270		ns
Turn-Off Fall Time	t _F				50		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Maximum Continuous Drain-Source Diode Forward Current	I _S				7	A	
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				28	A	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 7 A			1.4	V	
Body Diode Reverse Recovery Time	t _{rr}	I _S =7A, di/dt=100A/μs		400		ns	
Body Diode Reverse Recovery Charge	Q _{RR}				2.4		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

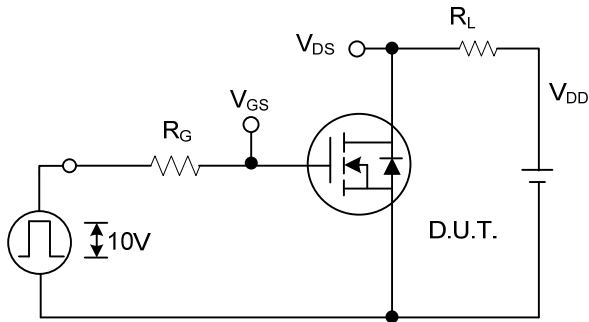


Peak Diode Recovery dv/dt Test Circuit

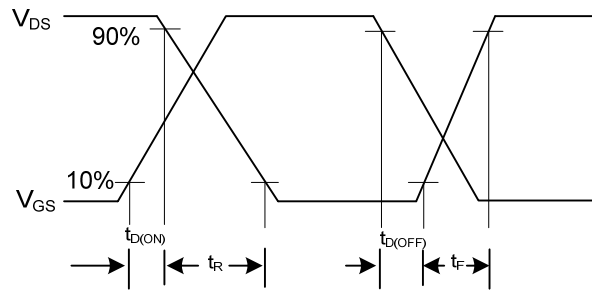


Peak Diode Recovery dv/dt Waveforms

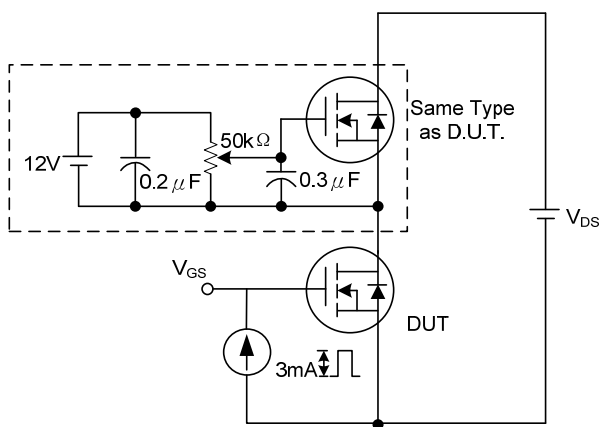
TEST CIRCUITS AND WAVEFORMS (Cont.)



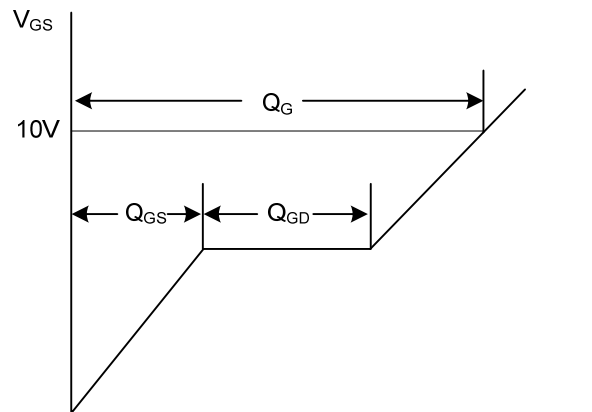
Switching Test Circuit



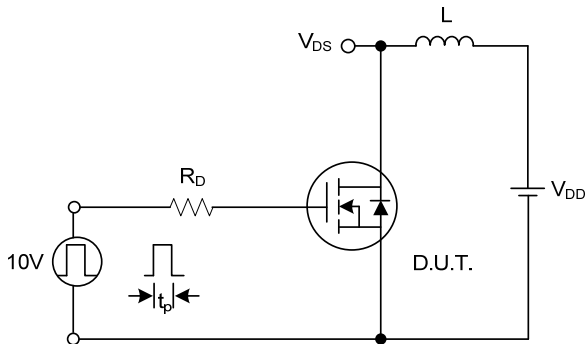
Switching Waveforms



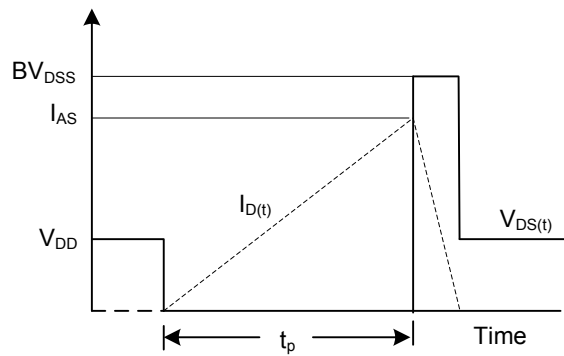
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.